CMOS Hex Buffers/Converters

High-Voltage Types (20-Volt Rating)

Inverting Type: CD4009UB
Non-Inverting Type: CD4010B

The RCA-CD4009UB and CD4010B Hex Buffer/Converters may be used as CMOS to TTL or DTL logic-level converters or CMOS high-sink-current drivers.

The CD4049UB and CD4050B are preferred hex buffer replacements for the CD4009UB and CD4010B, respectively, in all applications except multiplexers. For applications not requiring high sink current or voltage conversion, the CD4069UB Hex Inverter is recommended.

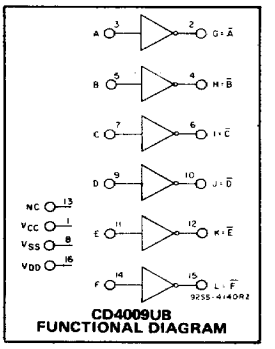
The CD4009UB and CD4010B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

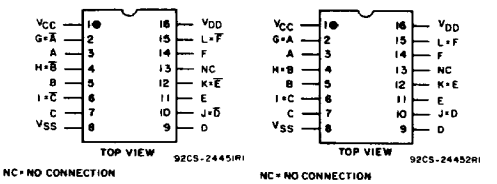
Features:

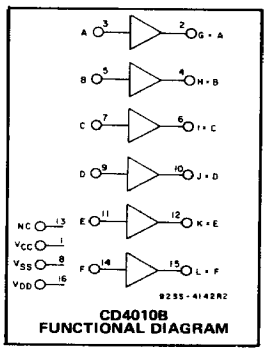
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings

Applications:

- CMOS to DTL/TTL hex converter
- CMOS current "sink" or "source" driver
- CMOS high-to-low logic-level converter
- Multiplexer — 1 to 6 or 6 to 1







TERMINAL ASSIGNMENTS

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD}, V_{CC}) (Voltages referenced to V_{SS} Terminal)	−0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	−0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT	±10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For T_A = −40 to +60°C (PACKAGE TYPE E)	500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
For T_A = −55 to +100°C (PACKAGE TYPES D, F, K)	500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H	−55 to +125°C
PACKAGE TYPE E	−40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg})	−65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max.	+265°C

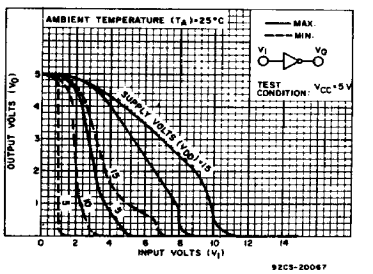


Fig. 3 — Minimum and maximum voltage transfer characteristics—CD4009UB.

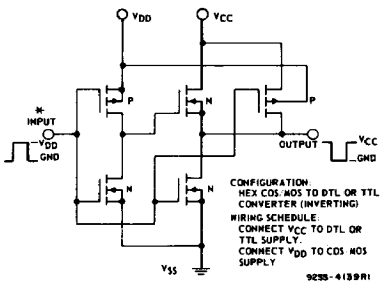


Fig. 1 — Schematic diagram of CD4009UB— 1 of 6 identical stages.

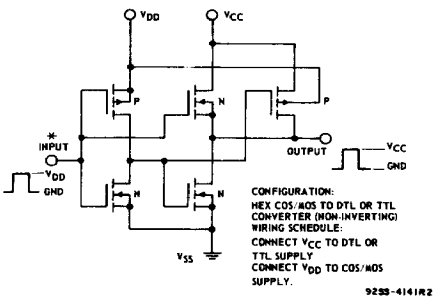
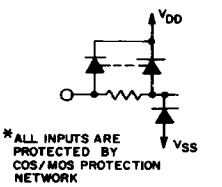


Fig. 2 — Schematic diagram of CD4010B— 1 of 6 identical stages.



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range), V_{DD}	3	18	V
V_{CC}*	3	V_{DD}	
Input Voltage Range (V_I)	V_{CC}*	V_{DD}	V

*The CD4009UB and CD4010B have high-to-low level voltage conversion capability but not low-to-high level, therefore it is recommended that $V_{DD} \geq V_I \geq V_{CC}$.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			Limits At Indicated Temperatures (°C) *Values at −55,+25,+125 Apply to D,F,K,H Pkgs. Values at −40,+25,+85 Apply to E Package*							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0.5	4.5	3.2	3.1	2.1	1.8	2.6	3.4	–	mA
	0.4	0,5	5	3.75	3.6	2.4	2.1	3	4	–	
	0.5	0,10	10	10	9.6	6.4	5.6	8	10	–	
	1.5	0,15	15	30	40	19	16	24	36	–	
Output High (Source) Current I_{OH} Min.	4.6	0,5	5	−0.25	−0.23	−0.18	−0.15	−0.2	−0.4	–	
	2.5	0,5	5	−1	−0.9	−0.65	−0.58	−0.8	−1.6	–	
	9.5	0,10	10	−0.55	−0.5	−0.38	−0.33	−0.45	−0.9	–	
	13.5	0,15	15	−1.65	−1.6	−1.25	−1.1	−1.5	−3	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05					0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage: V_{IL} Max. CD4009UB	4.5	–	5	1				–	–	1	V
	9	–	10	2				–	–	2	
	13.5	–	15	2.5				–	–	2.5	
Input Low Voltage: V_{IL} Max. CD4010B	0.5	–	5	1.5				–	–	1.5	
	1	–	10	3				–	–	3	
	1.5	–	15	4				–	–	4	
Input High Voltage: V_{IH} Min. CD4009UB	0.5	–	5	4				4	–	–	
	1	–	10	8				8	–	–	
	1.5	–	15	12.5				12.5	–	–	
Input High Voltage: V_{IH} Min. CD4010B	4.5	–	5	3.5				3.5	–	–	
	9	–	10	7				7	–	–	
	13.5	–	15	11				11	–	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

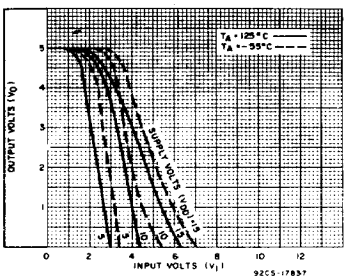


Fig. 4 – Typical voltage transfer characteristics as function of temp.–CD4009UB.

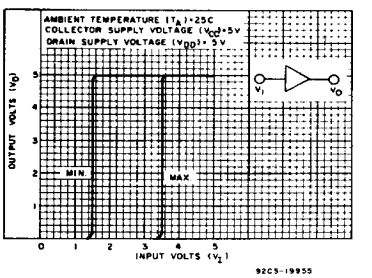


Fig. 5 – Minimum and maximum voltage transfer characteristics (V_{DD}=5)–CD4010B.

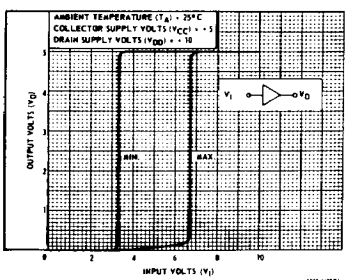


Fig. 6 – Minimum and maximum voltage transfer characteristics (V_{DD}=10)–CD4010B.

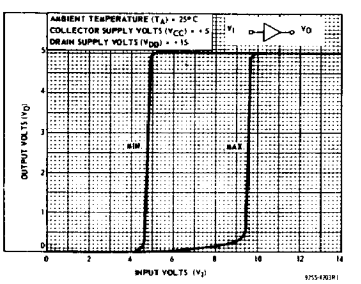


Fig. 7 – Minimum and maximum voltage transfer characteristics (V_{DD}=15)–CD4010B.

DYNAMIC ELECTRICAL CHARACTERISTICS *at T_A=25°C; Input t_r, t_f=20 ns, C_L=50 pF, R_L=200 KΩ*

CHARACTERISTIC	CONDITIONS V_{DD} (V)	V_I (V)	V_{CC} (V)	LIMITS ALL PKGS TYP.	MAX.	UNIT
Propagation Delay Time: Low-to-High, t_{PLH}	5	5	5	70	140	ns
	10	10	10	40	80	
CD4009UB	10	10	5	35	70	
	15	15	15	30	60	
	15	15	5	30	60	
	5	5	5	100	200	ns
	10	10	10	50	100	
CD4010B	10	10	5	50	100	
	15	15	15	35	70	
	15	15	5	35	70	
High-to-Low, t_{PHL}	5	5	5	30	60	ns
	10	10	10	20	40	
CD4009UB	10	10	5	15	30	
	15	15	15	15	30	
	15	15	5	10	20	
	5	5	5	65	130	ns
	10	10	10	35	70	
CD4010B	10	10	5	30	70	
	15	15	15	25	50	
	15	15	5	20	40	
Transition Time: Low-to-High, t_{TLH}	5	5	5	150	350	ns
	10	10	10	75	150	
	15	15	15	55	110	
High-to-Low, t_{THL}	5	5	5	35	70	ns
	10	10	10	20	40	
	15	15	15	15	30	
Input Capacitance, C_{IN} CD4009UB	–	–	–	15	22.5	pF
CD4010B	–	–	–	5	7.5	

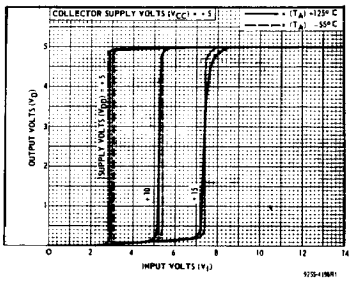


Fig. 8 – Typical voltage transfer characteristics as a function of temperature–CD4010B.

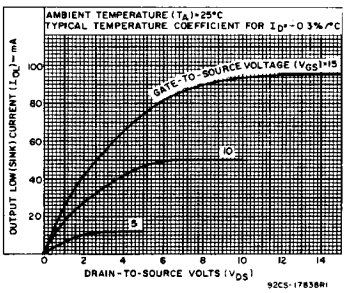


Fig. 9 – Typical output low (sink) current characteristics.

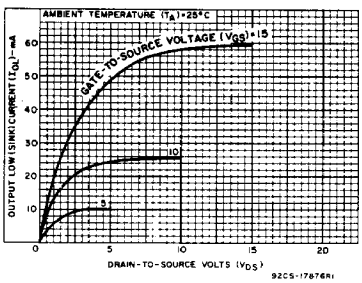


Fig. 10 – Minimum output low (sink) current characteristics.

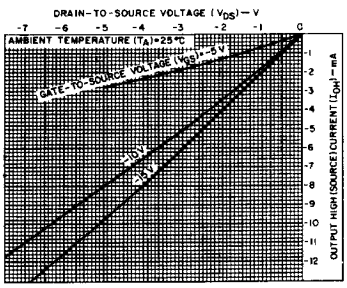


Fig. 11 – Typical output high (source) current characteristics.

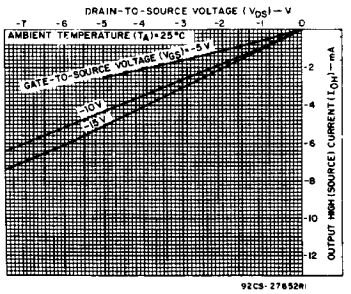


Fig. 12 – Minimum output high (source) current characteristics.

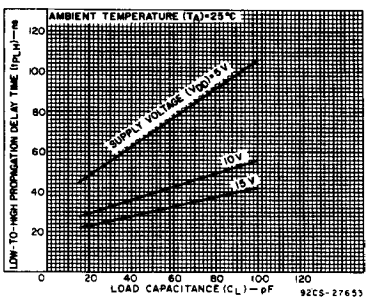


Fig. 13 – Typical low-to-high propagation delay time vs. load capacitance (CD4009UB).

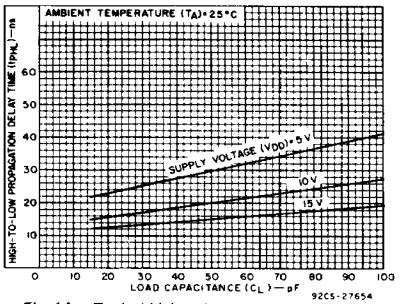


Fig. 14 — Typical high-to-low propagation delay time vs. load capacitance (CD4009UB).

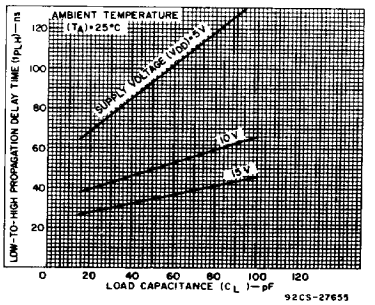


Fig. 15 — Typical low-to-high propagation delay time vs. load capacitance (CD4010B).

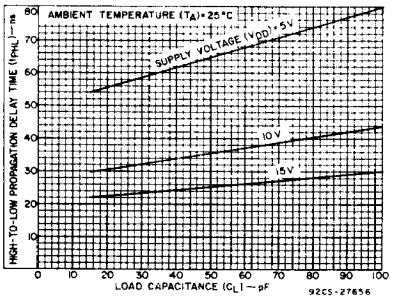


Fig. 16 — Typical high-to-low propagation delay time vs. load capacitance (CD4010B).

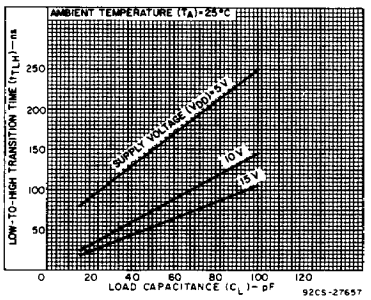


Fig. 17 — Typical low-to-high transition time vs. load capacitance.

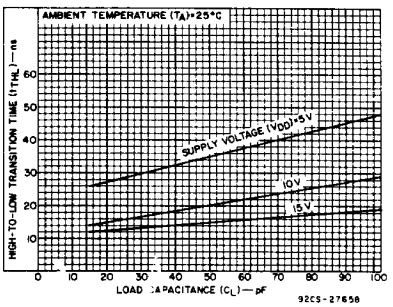


Fig. 18 — Typical high-to-low transition time vs. load capacitance.

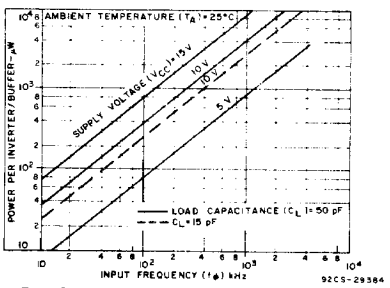


Fig. 19 — Typical dissipation charecteristics.

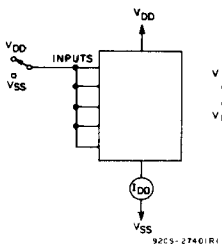


Fig. 20 — Quiescent device current test circuit.

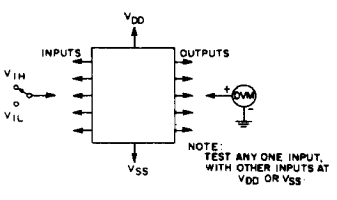
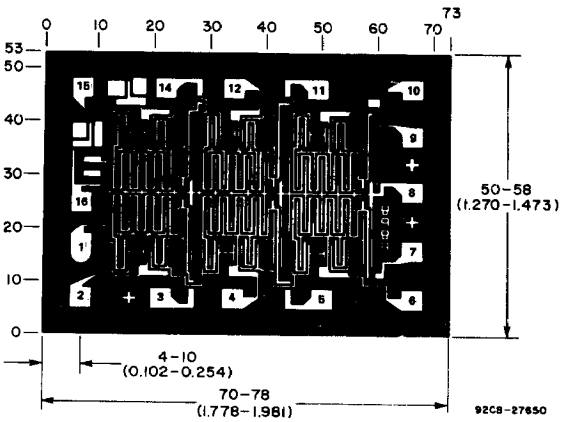


Fig. 21 — Noise immunity test circuit.



Photograph of chip for CD4009UB. Dimensions and pad layout for CD4010B are identical.

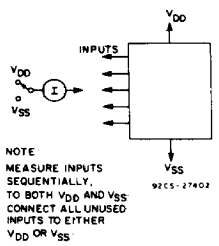


Fig. 22 — Input current test circuit.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid Graduations Are In Mils (10^{-3} Inch)

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.